



DMT2005UDV

DUAL 24V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UXC)

Product Summary

BV _{DSS}	R _{DS(ON) max}	Ι _D T _A = +25°C
24V	7mΩ @ V _{GS} = 10V	50
	$8m\Omega @ V_{GS} = 4.5V$	47
	$10m\Omega @ V_{GS} = 3.7V$	42
	$12m\Omega @ V_{GS} = 2.5V$	38

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- **Power Management Functions**
- Analog Switch

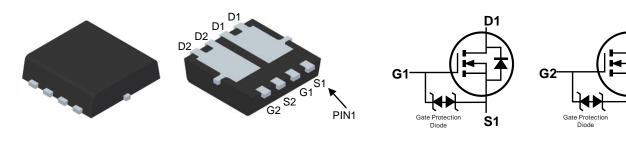
PowerDI3333-8 (Type UXC)

Features

- Low On-Resistance •
- Low Input Capacitance
- Fast Switching Speed .
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]3333-8 (Type UXC)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (Approximate)



Top View

Bottom View



Equivalent Circuit

Ordering Information (Note 4)

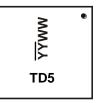
	Part Number	Case	Packaging		
	DMT2005UDV-7	PowerDI3333-8 (Type UXC)	2,000/Tape & Reel		
	DMT2005UDV-13 PowerDI3333-8 (Type UXC) 3000/Tape & Reel				
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.				

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



TD5 = Product Type Marking Code YYWW = Date Code Marking \overline{YY} = Last Two Digits of Year (ex: 18 for 2018) WW = Week Code (01 to 53)

D2

S2



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	24	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 7) V_{GS} = 10V	Steady State	T _C = +25°C T _C = +70°C	ID	50 40	A
Maximum Body Diode Forward Current (Note 7)			Is	30	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	70	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	70	A
Avalanche Current (Note 8) L = 0.1mH			I _{AS}	26	A
Avalanche Energy (Note 8) L = 0.1mH			E _{AS}	34	mJ

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	141	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	1.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	66	°C/W
Thermal Resistance, Junction to Case (Note 7)	·	R _{0JC}	4.8	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	24	_	_	V	$V_{GS} = 0V, I_{D} = 250 \mu A$	
Zero Gate Voltage Drain Current ($T_J = +25^{\circ}C$)	I _{DSS}	_	_	1	μA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	0.5	—	1.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
		—	5.9	7.0		$V_{GS} = 10V, I_D = 14A$	
Statia Duaia Causas On Desistance		—	6.3	8.0		V _{GS} = 4.5V, I _D = 14A	
Static Drain-Source On-Resistance	R _{DS(ON)}	—	6.7	10.0	mΩ	V _{GS} = 3.7V, I _D = 14A	
		—	8.9	12.0		V _{GS} = 2.5V, I _D = 13A	
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)	•		•			· · · ·	
Input Capacitance	Ciss	_	2,060	_		$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Output Capacitance	Coss	_	547	_	pF		
Reverse Transfer Capacitance	C _{rss}	—	517	_			
Gate Resistance	R _G	_	1.6		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	—	24.8	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	46.7	_	nC	V_{DD} = 10V, I_D = 5A	
Gate-Source Charge	Q _{gs}	-	3	_	nc		
Gate-Drain Charge	Q _{gd}	—	9.6	_			
Turn-On Delay Time	t _{D(ON)}	—	3.7	_		$V_{DD} = 10V, V_{GS} = 10V,$ $R_G = 3\Omega, I_D = 5A$	
Turn-On Rise Time	t _R	_	7.2	_	1		
Turn-Off Delay Time	t _{D(OFF)}	—	37.5		ns		
Turn-Off Fall Time	t _F	_	23.3				
Reverse Recovery Time	t _{RR}	—	19.9		ns		
Reverse Recovery Charge	Q _{RR}	—	9.0	—	nC	I _F = 5A, di/dt = 100A/µs	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

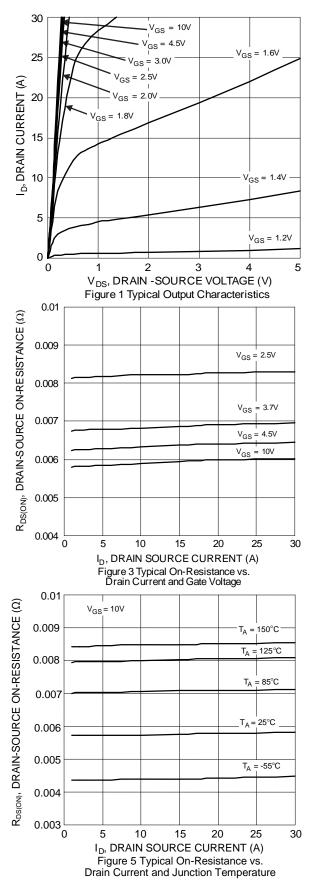
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).

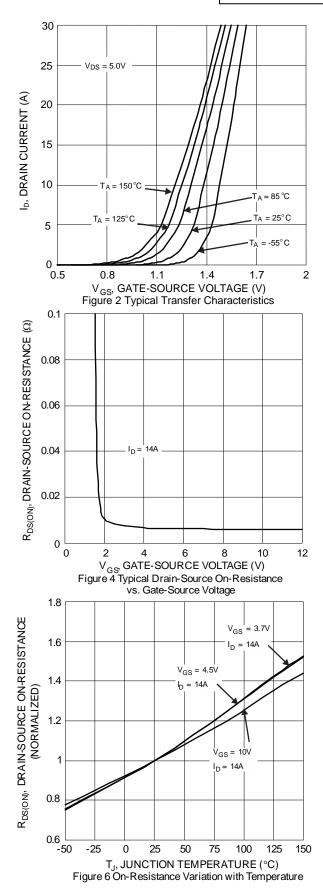
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.



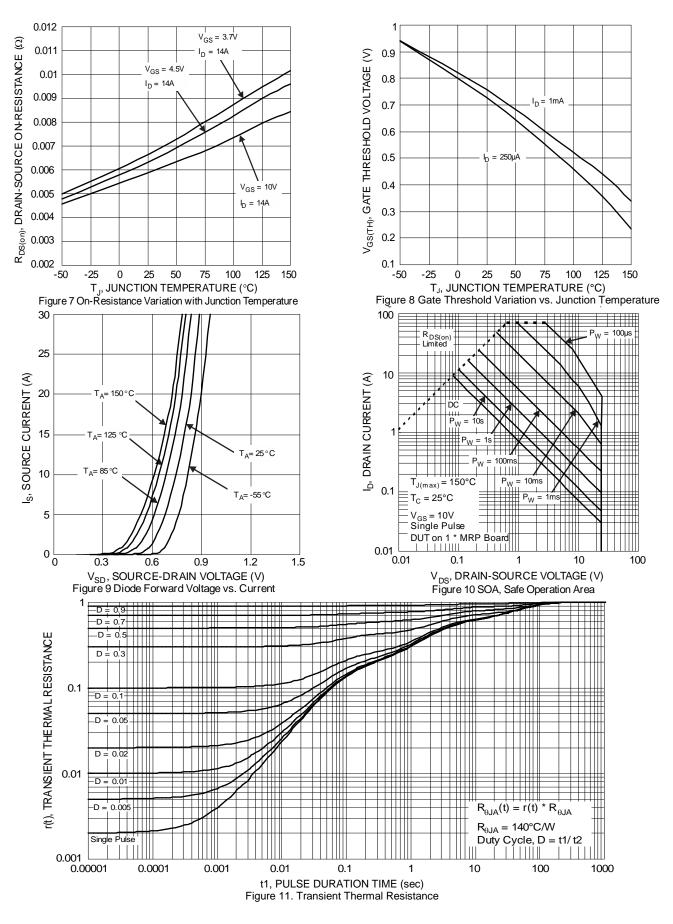




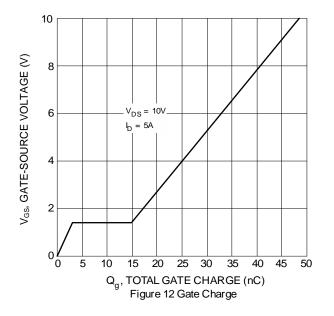


DMT2005UDV Document number: DS39727 Rev. 2 - 2







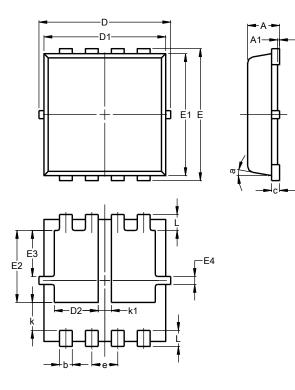




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UXC)

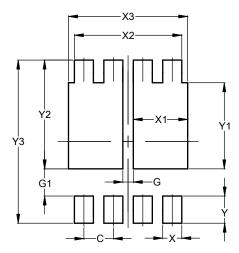


PowerDI3333-8 (Type UXC)					
Dim					
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	0.90	1.30	1.10		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е	-	-	0.65		
L	0.30	0.50	0.40		
k	0.50	0.90	0.70		
k1	0.13	0.53	0.33		
а	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UXC)



Dimensions	Value (in mm)
С	0.650
G	0.230
G1	0.600
Х	0.420
X1	1.200
X2	2.370
X3	2.630
Y	0.600
Y1	1.900
Y2	2.400
Y3	3.600



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